

2SA1797

PNP SILICON TRANSISTOR

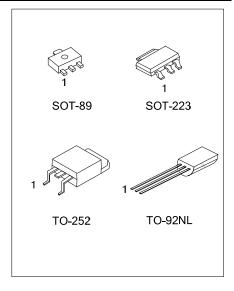
POWER TRANSISTOR

FEATURES

* Low Saturation Voltage.

 $V_{CE(SAT)}\text{=-}0.35V(MAX)$ at I_C / $I_B\text{=-}1A$ / -50mA

* Excellent DC Current Gain Characteristics

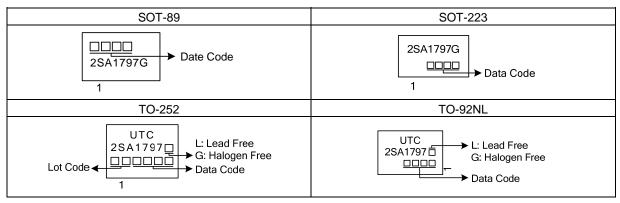


ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	2SA1797G-x-AA3-R	SOT-223	В	С	Е	Tape Reel	
-	2SA1797G-x-AB3-R	SOT-89	В	С	Е	Tape Reel	
2SA1797L-x-T9N-B	2SA1797G-x-T9N-B	TO-92NL	Е	С	В	Tape Box	
2SA1797L-x-T9N-K	2SA1797G-x-T9N-K	TO-92NL	E	С	В	Bulk	
2SA1797L-x-TN3-R	2SA1797G-x-TN3-R	TO-252	В	С	Е	Tape Reel	

Note: Pin Assignment: B: Base C: Collector E: Emitter

MARKING



PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	-50	V
Collector-Emitter Voltage		V _{CEO}	-50	V
Emitter-Base Voltage		V _{EBO}	-6	V
Collector Current	DC	I _C	-2	А
	PULSE(Note 1)		-5	А
Collector Power Dissipation	TO-92NL	Pc	1	W
	SOT-223		0.8	W
	SOT-89		0.5	W
	TO-252		1.9	W
Junction Temperature		TJ	150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

Note: 1. Single pulse, P_W=10ms

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = -50μA	-50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	$I_{C} = -1mA$	-50			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -50μA	-6			V
Collector Cutoff Current	I _{СВО}	V _{CB} = -50V			-0.1	μΑ
Emitter Cutoff Current	I _{EBO}	$V_{EB} = -5V$			-0.1	μΑ
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	$I_C/I_B = -1A/-50mA$ (Note)		-0.15	-0.35	V
DC Current Gain	h _{FE}	$V_{CE} = -2V, I_{C} = -0.5A$ (Note)	120		400	
Transition Frequency	f⊤	V _{CE} = -2V, I _E =0.5A, f=100MHz		200		MHz
Output Capacitance	C _{OB}	$V_{CB} = -10V, I_{E} = 0A, f = 1MHz$		36		pF

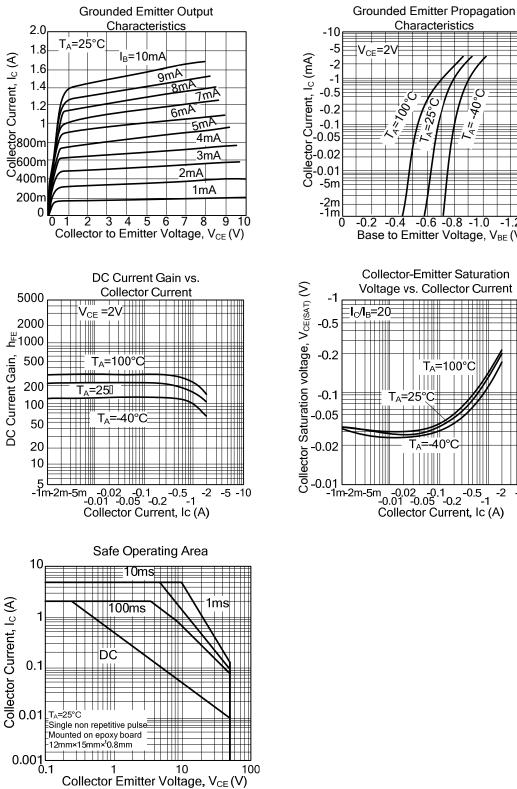
Note: Measured using pulse current.

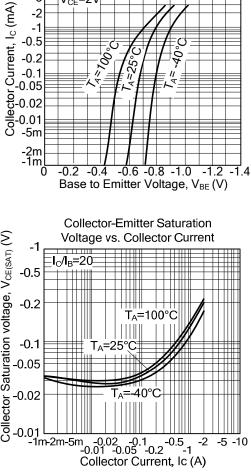
CLASSIFICATION OF h_{FE}

RANK	А	В
RANGE	120-240	200-400



TYPICAL CHARACTERISTICS







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